

**Europäisches Patentamt European Patent Office** Office européen des brevets



EP 1 452 481 A3

(12)

### **EUROPEAN PATENT APPLICATION**

(88) Date of publication A3: 12.10.2005 Bulletin 2005/41

(51) Int CL7: **B81B 7/00**, B81C 5/00, B81B 3/00, B81B 7/02

(11)

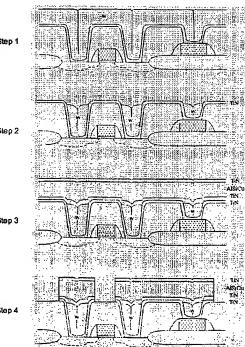
- (43) Date of publication A2: 01.09.2004 Bulletin 2004/36
- (21) Application number: 04100440.9
- (22) Date of filing: 05.02.2004
- (84) Designated Contracting States: AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IT LI LU MC NL PT RO SE SI SK TR **Designated Extension States:** AL LT LV MK
- (30) Priority: 07.02.2003 US 445426 P 13.02.2003 US 447019 P 10.04.2003 US 410158
- (71) Applicant: Dalsa Semiconductor Inc. Bromont, Quebec J2L 1S7 (CA)

- (72) Inventors:
  - Ouelett, Luc Granby, Quebec J2H 2R8 (CA)
  - Antaki, Robert St Luc, Quebec J2W 1W9 (CA)
- (74) Representative: Harding, Richard Patrick Marks & Clerk. 4220 Nash Court Oxford Business Park South Oxford OX4 2RU (GB)

#### (54)Fabrication of advanced silicon-based MEMS devices

A micro-electro-mechanical (MEM) device and an electronic device are fabricated on a common substrate by fabricating the electronic device comprising a plurality of electronic components on the common substrate, depositing a thermally stable interconnect layer on the electronic device, encapsulating the interconnected electronic device with a protective layer, forming a sacrificial layer over the protective layer, opening holes in the sacrificial layer and the protective layer to allow the connection of the MEM device to the electronic device, fabricating the MEM device by depositing and patterning at least one layer of amorphous silicon, and removing at least a portion of the sacrificial layer. In this way, the MEM device can be fabricated after the electronic device on the same substrate.

Figure 14 Interconnection strategy allowing the fabrication of advanced MEMS after the integrated circuit





## **EUROPEAN SEARCH REPORT**

Application Number EP 04 10 0440

atacas	Citation of document with indicat	ion, where appropriate.	Relevant	CLASSIFICATION OF THE	
Category	of relevant passages	,	to claim	APPLICATION (Int.CI.7)	
Α	DE 198 29 609 A1 (ROBE 5 January 2000 (2000-0 * column 2, line 6 - 1 * column 3, line 50 - * claim 1 *	1,11,14	B81B7/00 B81C5/00 B81B3/00 B81B7/02		
<b>A</b>	XIE H ET AL: "Vertical capacitive actuation and CMOS-MEMS" SENSORS AND ACTUATORS S.A., LAUSANNE, CH, vol. 95, no. 2-3, 1 January 2002 (2002-0212-221, XP004377894 ISSN: 0924-4247 * figure 1 * paragraph "1. Introductions"	nd sensing for A, ELSEVIER SEQUOIA 11-01), pages	1		
A	FRANKE A E ET AL: "Po of germanium microstru MICRO ELECTRO MECHANIO MEMS '99. TWELFTH IEEE CONFERENCE ON ORLANDO, 1999, PISCATAWAY, NJ, 17 January 1999 (1999- 630-637, XP010321723 ISBN: 0-7803-5194-0 * figure 7 * * abstract * paragraph "1. introduc	1	TECHNICAL FIELDS SEARCHED (Int.Cl.7) B81B		
		-/	1		
		,			
			1		
	The present search report has been	drawn up for all claims	,	,	
	Place of search	Date of completion of the search	ــــــــــــــــــــــــــــــــــــــ	Examine	
	Berlin	10 August 2005	Mei	ster, M	
X : part Y : part docu	ATEGORY OF CITED DOCUMENTS ioularly relevant if taken alone ioularly relevant if combined with another iment of the same category inological background -written disclosure	T : theory or principl E : earlier patent do after the filing dat D : document ofted I L : document ofted f	e underlying the in pument, but publis e n the application or other reasons	nvention	



# **EUROPEAN SEARCH REPORT**

Application Number EP 04 10 0440

Category	Citation of document with indicat	ion, where appropriate,	Relevant	CLASSIFICATION OF THE
Α	of relevant passages  FONASH S J: "Integrat electronics and MEMs"		to claim	APPLICATION (Int.Cl.7)
	PROCEEDINGS OF THE SPI vol. 2722, 28 February pages 66-74, XP0023400 USA	1996 (1996-02-28).		
	* figure 3 * paragraph "3. Material issues"	s and processing		
A	FORTIN V ET AL: "Effe oxidation of TiN diffu AlSiCu/TiN/Ti metalliz integrated circuits" JOURNAL OF VACUUM SCIE MICROELECTRONICS PROCE	sion barrier for ation structure of NCE & TECHNOLOGY B: SSING AND PHENOMENA,		
	AMERICAN VACUUM SOCIET vol. 17, no. 2, March pages 423-431, XP01200 ISSN: 0734-211X * abstract *	1999 (1999-03),		TECHNICAL FIELDS
	paragraph "1. Introduc	tion"		SEARCHED (Int.Cl.7)
D,A	US 6 127 266 A (OUELLE 3 October 2000 (2000-1 * column 1, line 10 - * column 6, line 28 -	0-03) column 2, line 63 *	3,4,6,7	
	••			
	The present search report has been o	•		
	Place of search Berlin	Date of completion of the search 10 August 2005	Mei	Examiner Ster, M
X : parti Y : parti docu	TEGORY OF CITED DOCUMENTS  cularly relevant if taken alone  oularly relevant if combined with another  ment of the same category  tological background	T: theory or principle E: earlier patent doc after the filing dat D: document cited if L: document cited fi	a underlying the in cument, but publish e n the application	vention

### EP 1 452 481 A3

### ANNEX TO THE EUROPEAN SEARCH REPORT ON EUROPEAN PATENT APPLICATION NO.

EP 04 10 0440

This annex lists the patent family members relating to the patent documents cited in the above-mentioned European search report. The members are as contained in the European Patent Office EDP file on The European Patent Office is in no way liable for these particulars which are merely given for the purpose of information.

10-08-2005

Patent document cited in search report		Publication date		Patent family member(s)		Publication date
DE 19829609	A1	05-01-2000	NONE		<u></u>	
US 6127266	A	03-10-2000	CA WO EP JP	2191260 9824116 0902968 11509692	Al Al	26-05-199 04-06-199 24-03-199 24-08-199
÷	par.		•			
		·				
•						

For more details about this annex : see Official Journal of the European Patent Office, No. 12/82